



# STP60NE03L-12

N - CHANNEL 30V - 0.009  $\Omega$  - 60A - T0-220  
STripFET™ POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STP60NE03L-12	30 V	< 0.012 $\Omega$	60 A

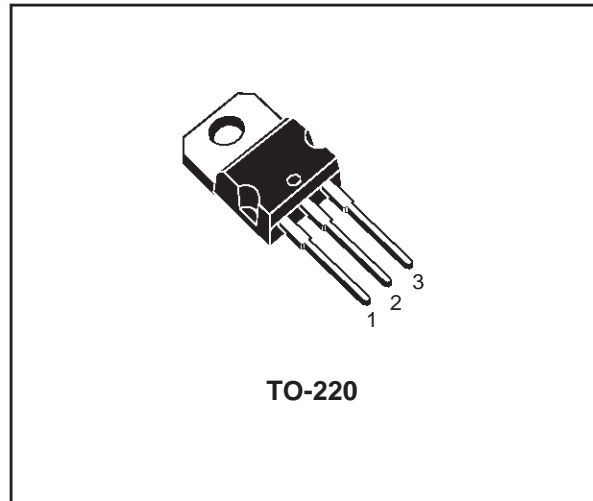
- TYPICAL R<sub>DS(on)</sub> = 0.009  $\Omega$
- AVALANCE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100 °C
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- 175 °C OPERATING TEMPERATURE
- APPLICATION ORIENTED CHARACTERIZATION

## DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

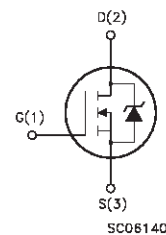
## APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- DC-DC & DC-AC CONVERTERS
- AUTOMOTIVE ENVIRONMENT



TO-220

## INTERNAL SCHEMATIC DIAGRAM



## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	30	V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 k $\Omega$ )	30	V
V <sub>GS</sub>	Gate-source Voltage	$\pm 20$	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	60	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	42	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	240	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	100	W
	Derating Factor	0.67	W/°C
dv/dt	Peak Diode Recovery voltage slope	5.5	V/ns
T <sub>stg</sub>	Storage Temperature	-65 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

(1) I<sub>SD</sub>  $\leq$  60 A, di/dt  $\leq$  450 A/ $\mu$ s, V<sub>DD</sub>  $\leq$  V<sub>(BR)DSS</sub>, T<sub>j</sub>  $\leq$  T<sub>JMAX</sub>

## THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	1.5	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	62.5	$^{\circ}C/W$
$R_{thc-sink}$	Thermal Resistance Case-sink	Typ	0.5	$^{\circ}C/W$
$T_I$	Maximum Lead Temperature For Soldering Purpose		300	$^{\circ}C$

## AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
$I_{AR}$	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by $T_j$ max)	60	A
$E_{AS}$	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$ , $I_D = I_{AR}$ , $V_{DD} = 15 V$ )	250	mJ

ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^{\circ}C$  unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A$ $V_{GS} = 0$	30			V
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 125^{\circ}C$			1 10	$\mu A$ $\mu A$
$I_{GSS}$	Gate-body Leakage Current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20 V$			$\pm 100$	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$	1	1.7	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V$ $I_D = 30 A$ $V_{GS} = 5V$ $I_D = 30 A$		0.009	0.012 0.018	$\Omega$
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10 V$	60			A

## DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 30 A$	20	30		S
$C_{iss}$	Input Capacitance	$V_{DS} = 25 V$ $f = 1 MHz$ $V_{GS} = 0$		2200		pF
$C_{oss}$	Output Capacitance			570		pF
$C_{rss}$	Reverse Transfer Capacitance			200		pF

**ELECTRICAL CHARACTERISTICS** (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 15\text{ V}$ $I_D = 30\text{ A}$		40		ns
$t_r$	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$ (Resistive Load, see fig. 3)		260		ns
$Q_g$	Total Gate Charge	$V_{DD} = 24\text{ V}$ $I_D = 60\text{ A}$ $V_{GS} = 5\text{ V}$		35	45	nC
$Q_{gs}$	Gate-Source Charge			18		nC
$Q_{gd}$	Gate-Drain Charge			13		nC

**SWITCHING OFF**

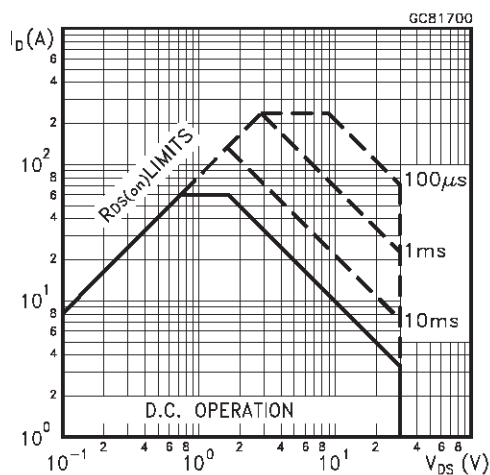
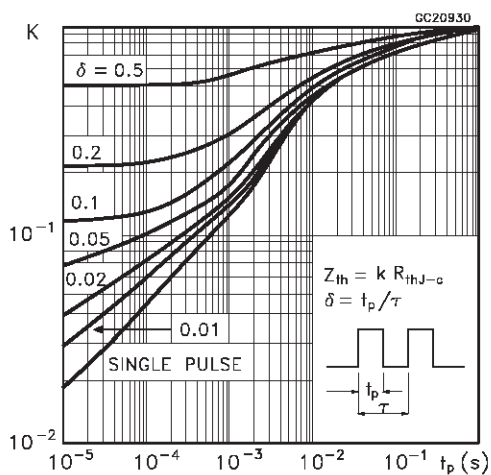
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 15\text{ V}$ $I_D = 30\text{ A}$		75		ns
$t_f$	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 5\text{ V}$ (Resistive Load, see fig. 3)		50		ns
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 24\text{ V}$ $I_D = 60\text{ A}$		35		ns
$t_f$	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 15\text{ V}$		120		ns
$t_c$	Cross-over Time	(Inductive Load, see fig. 5)		175		ns

**SOURCE DRAIN DIODE**

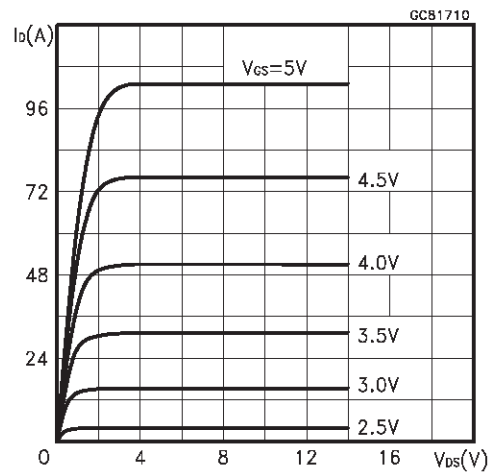
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				60	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				240	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 60\text{ A}$ $V_{GS} = 0$			1.5	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 60\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 15\text{ V}$ $T_J = 150\text{ }^\circ\text{C}$ (see test circuit, fig. 5)		55		ns
$Q_{rr}$	Reverse Recovery Charge			0.1		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			3.5		A

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

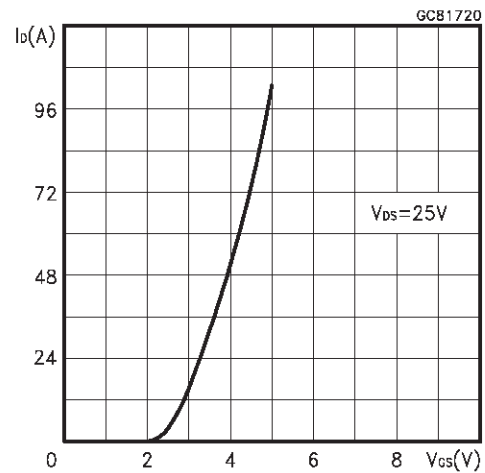
(\bullet) Pulse width limited by safe operating area

**Safe Operating Area****Thermal Impedance**

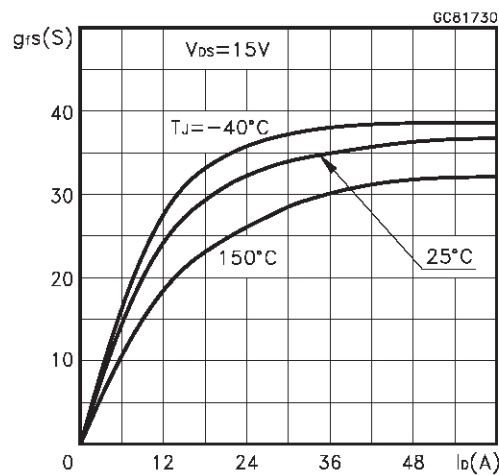
Output Characteristics



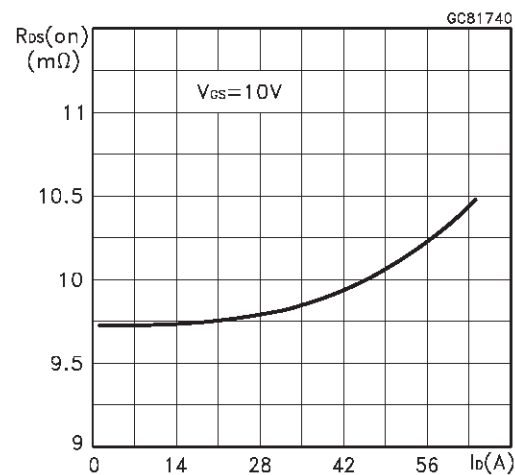
Transfer Characteristics



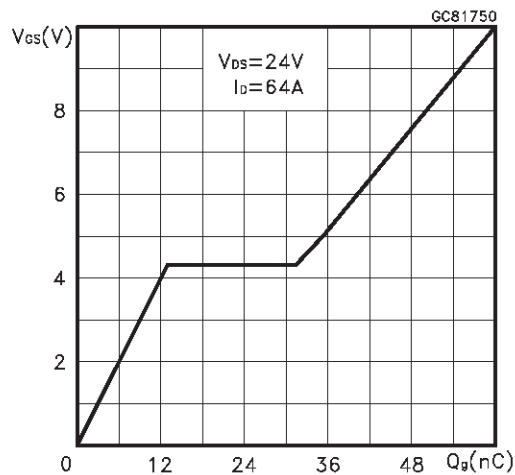
Transconductance



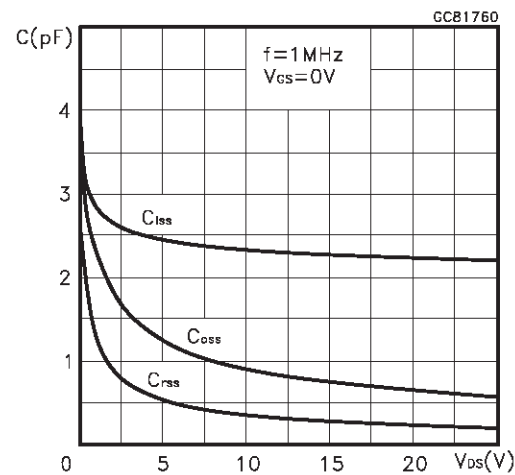
Static Drain-source On Resistance



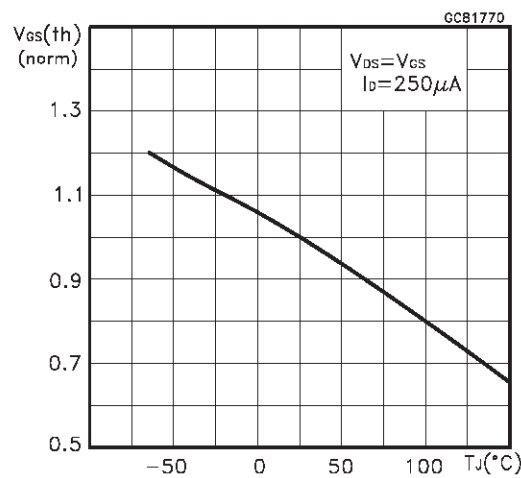
Gate Charge vs Gate-source Voltage



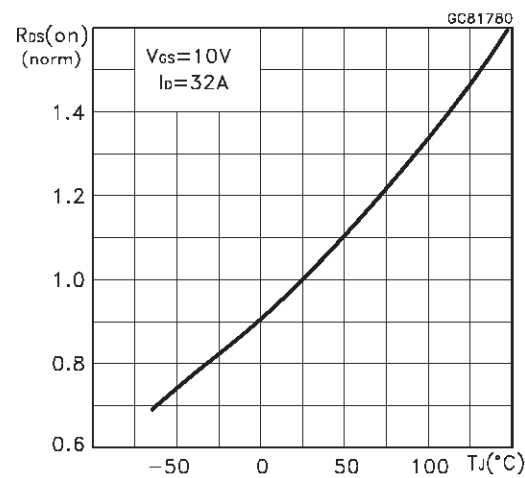
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

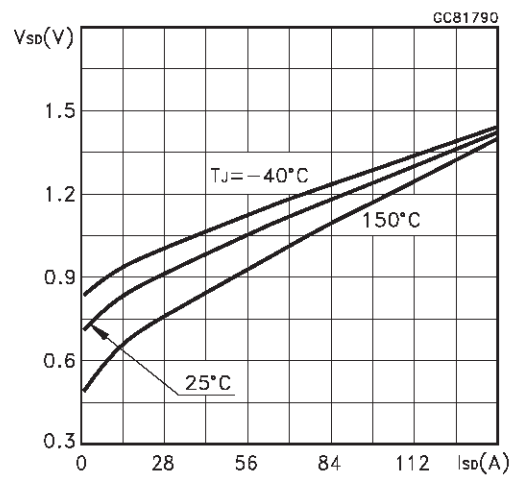


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform



Fig. 3: Switching Times Test Circuits For Resistive Load



Fig. 4: Gate Charge test Circuit

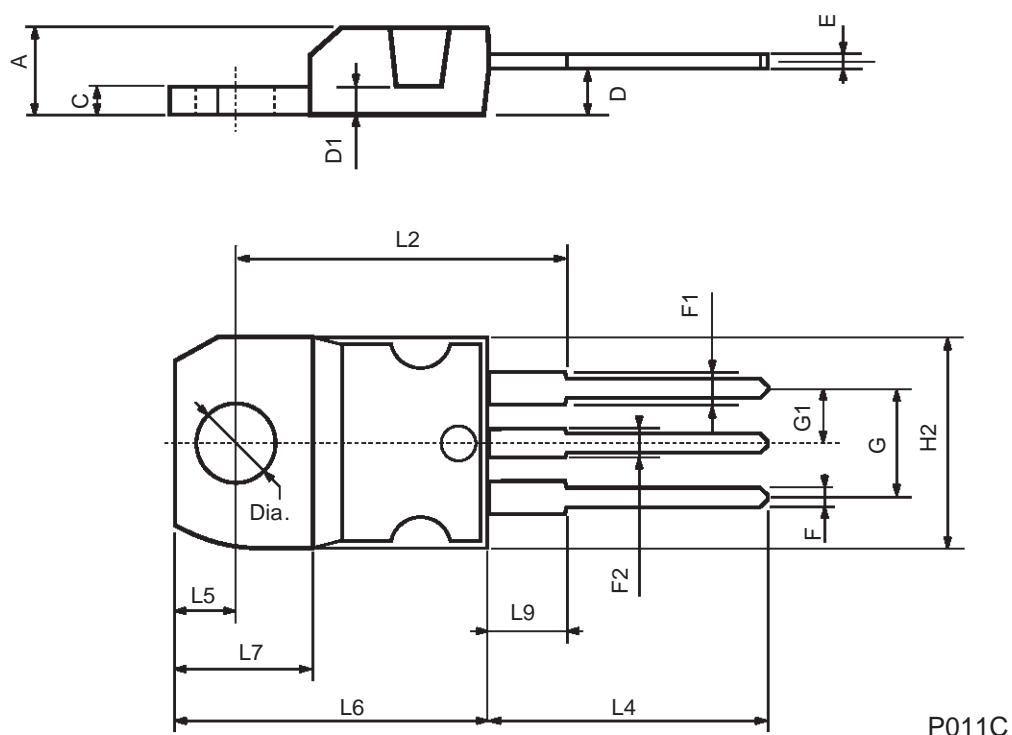


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



## TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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